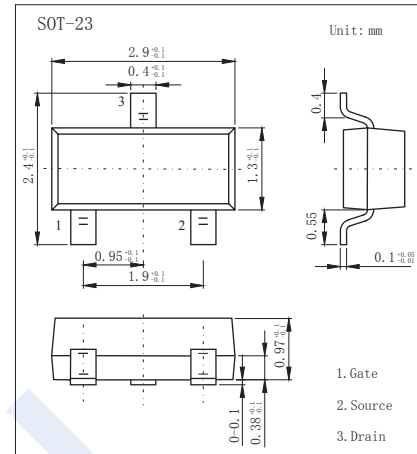


P-Channel Enhancement MOSFET

KI005P

■ Features

- $V_{DS} (V) = -20V$
- $I_D = -2.8 A$
- $R_{DS(ON)} < 115m\Omega$ ($V_{GS} = -4.5V$)
- $R_{DS(ON)} < 160m\Omega$ ($V_{GS} = -2.5V$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current	I_D	-2.8	A
Power Dissipation	P_D	1.2	W
Junction Temperature	T_J	150	$^\circ C$
Junction and Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D = -250 \mu A, V_{GS} = 0V$	-20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V, T_J = 25^\circ C$			1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 12V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.4	-0.7	-1.1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -1A$			115	m Ω
		$V_{GS} = -2.5V, I_D = -0.5A$			160	

■ Marking

Marking	005P
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